# Power Transistor (400V, 0.1A)

# 2SC4505

### Features

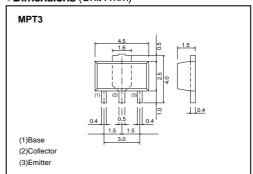
- 1) High breakdown voltage. (BVcEo = 400V)
- 2) Low saturation voltage, typically  $V_{CE (sat)} = 0.05V$  at  $I_C / I_B = 10mA / 1mA$ .
- 3) High switching speed, typically tf = 1.7 $\mu$ s at Ic =100mA.
- 4) Complements the 2SC4505 and the 2SA1759.

### Packaging specifications and hfe

Туре	2SC4505		
Package	MPT3		
hfE	PQ		
Marking	CE*		
Code	T100		
Basic ordering unit (pieces)	1000		

<sup>\*</sup> Denotes her

### ●Dimensions (Unit:mm)



### ● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	400	V	
Collector-emitter voltage	VCEO	400	V	
Emitter-base voltage	Vево	7	V	
Collector current	lc	0.1	A (DC)	
		0.2	A (Pulse) *1	
Collector power dissipation	D.	0.5	W	
	Pc	2	W *2	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

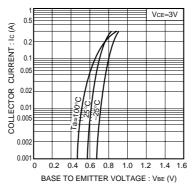
<sup>\*1</sup> Single pulse, Pw=20ms, Duty=1/2

### ●Electrical characteristics (Ta=25°C)

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Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	400	-	-	V	Ic=50μA
Collector-emitter breakdown voltage	BVceo	400	-	-	V	Ic=1mA
Emitter-base breakdown voltage	ВУево	7	-	-	V	Iε=50μA
Collector cutoff current	Ісво	-	-	10	μА	Vcb=400V
Emitter cutoff current	ІЕВО	-	-	10	μА	V <sub>EB</sub> =6V
Collector-emitter saturation voltage	VcE(sat)	-	0.05	0.5	V	Ic/I <sub>B</sub> =10mA/1mA
Base-emitter saturation voltage	V <sub>BE</sub> (sat)	-	-	1.5	V	Ic/I <sub>B</sub> =10mA/1mA
DC current transfer ratio	hfe	82	-	270	-	Vce=10V , Ic=10mA
Transition frequency	fτ	-	20	-	MHz	Vce=10V , Ie=-10mA , f=10MHz
Output capacitance	Cob	-	7	-	pF	Vcb=10V , IE=0A , f=1MHz
Turn-on time	ton	-	1	-	μs	Ic=-100mA R <sub>L</sub> =1.5kΩ
Storage time	tstg	-	5.5	-	μs	Iв1=-Iв2=10mA
Fall time	tr	-	1.7	-	μs	Vcc <sub>~</sub> -150V

<sup>\*2</sup> When mounted on a 40×40×0.7mm ceramic board.

# PElectrical characteristics (Ta=25°C) 200 Ta=25°C Ta=25°C



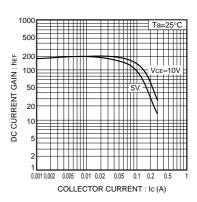
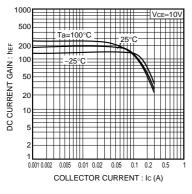
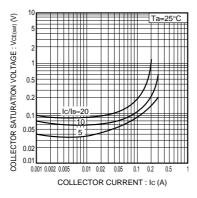


Fig.1 Ground emitter output characteristics

Fig.2 Ground emitter propagation characterisitics

Fig.3 DC current gain vs. collector current (I)





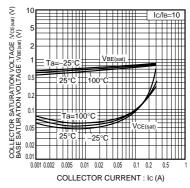


Fig.4 DC current gain vs. collector current ( II )

Fig.5 Collector-emitter saturation voltage vs. collector current

Fig.6 Collector-emitter saturation voltage Collector-base saturation voltage vs. collector current

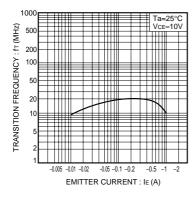


Fig.7 Gain bandwidth product vs. emitter current

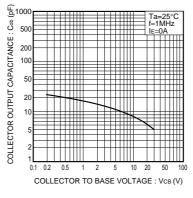


Fig.8 Collector output capacitance vs. collector-base voltage

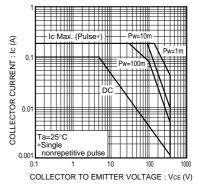


Fig.9 Safe operating area

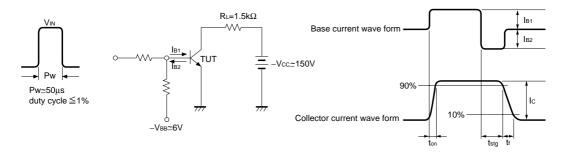


Fig.10 Switching time mesurement circuit

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